

Peter Lagov

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

22
papers

203
citations

8
h-index

14
g-index

26
ext. papers

255
ext. citations

1.9
avg, IF

2.67
L-index

#	Paper	IF	Citations
22	Hole traps and persistent photocapacitance in proton irradiated GaN films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50
21	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated GaN . <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
20	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. <i>Journal of Applied Physics</i> , 2017 , 122, 115704	2.5	19
19	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. <i>Journal of Applied Physics</i> , 2019 , 126, 125708	2.5	14
18	Pulsed fast reactor neutron irradiation effects in Si doped n-type GaN . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
17	Electron irradiation of near-UV GaN/InGaN light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700372	1.6	10
16	Deep Electron and Hole Traps in Electron-Irradiated Green GaN/InGaN Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q127-Q131	2	9
15	Defect States Induced in GaN-Based Green Light Emitting Diodes by Electron Irradiation. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P323-P328	2	9
14	Accelerator-based electron beam technologies for modification of bipolar semiconductor devices. <i>Journal of Physics: Conference Series</i> , 2016 , 747, 012085	0.3	8
13	Magnetic Buncher Accelerator for Radiation Hardness Research and Pulse Detector Characterization 2015 ,		5
12	Nanosilicon stabilized with ligands: Effect of high-energy electron beam on luminescent properties. <i>Surface and Interface Analysis</i> , 2020 , 52, 957-961	1.5	4
11	Crystal orientation dependence of deep level spectra in proton irradiated bulk GaN . <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
10	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 445111	3	3
9	Particularities of Vanadium Microstructure Development During Irradiation by 7.5 MeV Ni^{2+} Ions at 650°C. <i>Atomic Energy</i> , 2015 , 118, 400-404	0.4	2
8	Proton-irradiation technology for high-frequency high-current silicon welding diode manufacturing. <i>Journal of Physics: Conference Series</i> , 2017 , 830, 012152	0.3	1
7	Development of Gas Porosity along the Ion Range in Vanadium Alloys during Sequential Helium and Hydrogen Ion Irradiation. <i>Russian Metallurgy (Metally)</i> , 2019 , 2019, 1161-1166	0.5	1
6	1 GeV proton damage in GaN . <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1

- 5 Effect of Electron Irradiation on the Optical Properties of Gadolinium-Aluminum-Gallium Garnet Crystals. *Journal of Surface Investigation*, **2021**, 15, 1259-1263 0.5 0
- 4 Laser ion source for semiconductor applications. *Journal of Physics: Conference Series*, **2022**, 2244, 0120963 0
- 3 Features of Gas Porosity Formation Along Helium Ion Trajectories in Vanadium Alloys. *Atomic Energy*, **2019**, 126, 46-51 0.4
- 2 Detection of Unreliable Superluminescent Diode Chips Using Gamma-Irradiation. *Lecture Notes in Mechanical Engineering*, **2019**, 309-317 0.4
- 1 Comparison of the Helium Porosity Parameters in Vanadium Alloy TEM Samples Prepared by Various Techniques. *Russian Metallurgy (Metally)*, **2020**, 2020, 206-211 0.5